V_{DRM}	=	8500 V
$I_{T(AV)M}$	=	2660 A
$I_{T(RMS)}$	=	4180 A
I_{TSM}	=	$64.0 \cdot 10^3$ A
V_{T0}	=	1.13 V
r_T	=	0.394 mΩ

Phase Control Thyristor

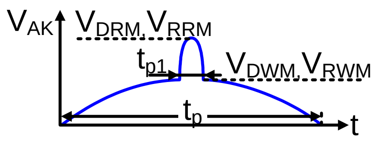
5STP 27N8500

Doc. No. 5SYA1077-04 May. 20

- **Patented free-floating silicon technology**
- **Low on-state and switching losses**
- **Designed for traction, energy and industrial applications**
- **Optimum power handling capability**
- **Interdigitated amplifying gate**

Blocking

***Maximum rated values* [1)]**

Parameter	Symbol	Conditions	5STP 27N8500	Unit
Max. surge peak forward and reverse blocking voltage	V_{DSM}, V_{RSM}	t_p = 10 ms, f = 5 Hz T_{vj} = 25…125 °C, Note 1	8500	V
Max repetitive peak forward and reverse blocking voltage	V_{DRM}, V_{RRM}	f = 50 Hz, t_p = 10 ms, t_{p1} = 250 µs, T_{vj} = 25…125 °C, Note 1, Note 2	8500	V
Max crest working forward and reverse voltages	V_{DWM}, V_{RWM}		5670	V
Critical rate of rise of commutating voltage	dv/dt_{crit}	Exp. to $0.67 \cdot V_{DRM}$, T_{vj} = 125 °C	3000	V/µs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward leakage current	I_{DRM}	V_{DRM}, T_{vj} = 125 °C		300	600	mA
Reverse leakage current	I_{RRM}	V_{RRM}, T_{vj} = 125 °C		300	600	mA

Note 1: Voltage de-rating factor of 0.11% per °C is applicable for T_{vj} below +25 °C.
Note 2: Recommended minimum ratio of V_{DRM} / V_{DWM} or V_{RRM} / V_{RWM} = 2. See App. Note 5SYA 2051.

Mechanical data

***Maximum rated values* [1)]**

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		81	90	108	kN
Acceleration	a	Device unclamped			50	m/s^2
Acceleration	a	Device clamped			100	m/s^2

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				2.9	kg
Housing thickness	H	F_M = 90 kN, T_a = 25 °C	35.19		35.84	mm
Surface creepage distance	D_S		56			mm
Air strike distance	D_a		22			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

On-state

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Average on-state current	$I_{T(AV)M}$	Half sine wave, Tc = 70 °C			2660	A
RMS on-state current	$I_{T(RMS)}$				4180	A
Peak non-repetitive surge current	I_{TSM}	t_p = 10 ms, T_{vj} = 125 °C, sine half wave, V_D = V_R= 0 V, after surge			$64.0 \cdot 10^3$	A
Limiting load integral	I^2t				$20.5 \cdot 10^6$	A^2s
Peak non-repetitive surge current	I_{TSM}	t_p = 10 ms, T_{vj} = 125 °C, sine half wave, V_R = 0.6·V_{RRM}, after surge			$33.6 \cdot 10^3$	A
Limiting load integral	I^2t				$5.64 \cdot 10^6$	A^2s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_T	I_T = 1500 A, T_{vj} = 125 °C		1.54	1.72	V
Threshold voltage	$V_{(T0)}$	I_T = 800 A - 3000 A, T_{vj} = 125 °C		1.01	1.13	V
Slope resistance	r_T			0.356	0.394	mΩ
Holding current	I_H	T_{vj} = 25 °C			160	mA
		T_{vj} = 125 °C			80	mA
Latching current	I_L	T_{vj} = 25 °C			500	mA
		T_{vj} = 125 °C			250	mA

Switching

Maximum rated values [1)]

Parameter	Symbol	Conditions		min	typ	max	Unit
Critical rate of rise of on-state current	di/dt_{crit}	T_{vj} = 125 °C, I_T = 2000 A, $V_D \leq 0.67 \cdot V_{DRM}$, I_{GM} = 2 A, t_r = 0.5 µs	Cont. f = 50 Hz			300	A/µs
			Cont. f = 1 Hz			1000	A/µs
Circuit-commutated turn-off time	t_q	T_{vj} = 125 °C, I_T = 2000 A, V_R = 200 V, di_T/dt = -1.5 A/µs, $V_D \leq 0.67 \cdot V_{DRM}$, dv_D/dt = 20 V/µs			550	800	µs

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery charge	Q_{rr}	T_{vj} = 125 °C, I_T = 2000 A, V_R = 200 V, di_T/dt = -1.5 A/µs	4000	5890	7000	µAs
Reverse recovery current	I_{RM}		55	77	95	A
Gate turn-on delay time	t_{gd}	T_{vj} = 25 °C, V_D = 0.4·V_{RM}, I_{GM} = 2 A, t_r = 0.5 µs			3	µs

Triggering

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward gate voltage	V_{FGM}				12	V
Peak forward gate current	I_{FGM}				10	A
Peak reverse gate voltage	V_{RGM}				10	V
Average gate power loss	$P_{G(AV)}$		see Fig. 7			W

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Gate-trigger voltage	V_{GT}	T_{vj} = 25 °C			2.6	V
Gate-trigger current	I_{GT}	T_{vj} = 25 °C			400	mA
Gate non-trigger voltage	V_{GD}	$V_D = 0.4 \cdot V_{DRM}$, T_{vjmax} = 125 °C			0.3	V
Gate non-trigger current	I_{GD}	$V_D = 0.4 \cdot V_{DRM}$, T_{vjmax} = 125 °C			10	mA

Thermal

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T_{vj}				125	°C
Storage temperature range	T_{stg}		-40		140	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled F_m = 81... 108 kN			5.7	K/kW
	$R_{th(j-c)A}$	Anode-side cooled F_m = 81... 108 kN			11.4	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled F_m = 81... 108 kN			11.4	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled F_m = 81... 108 kN			1	K/kW
	$R_{th(c-h)}$	Single-side cooled F_m = 81... 108 kN			2	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^{n} R_i \left(1 - e^{-t/\tau_i}\right)$$

i	1	2	3	4
R_i(K/kW)	3.939	1.264	0.490	0.007
τ_i(s)	0.7962	0.0870	0.0083	0.0004

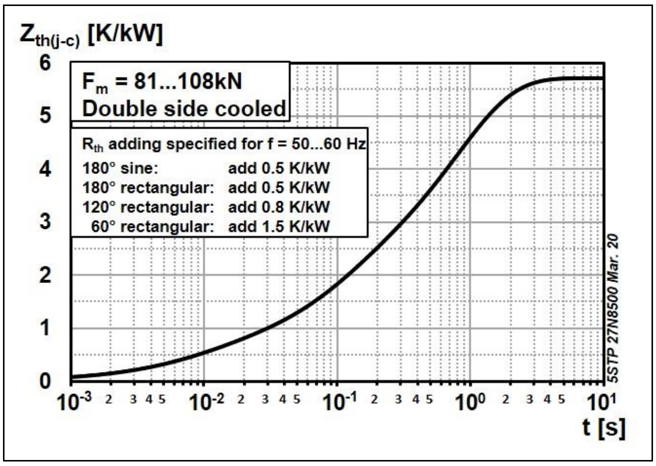


Fig. 1 Transient thermal impedance (junction-to-case) vs. time

Max. on-state characteristic model:

$$V_{T25} = A_{Tvj} + B_{Tvj} \cdot I_T + C_{Tvj} \cdot \ln(I_T + 1) + D_{Tvj} \cdot \sqrt{I_T}$$

Valid for I_T = 1000 - 70000 A

A_{25}	B_{25}	C_{25}	D_{25}
$112.6 \cdot 10^{-3}$	$142.2 \cdot 10^{-6}$	$173.5 \cdot 10^{-3}$	$3.043 \cdot 10^{-3}$

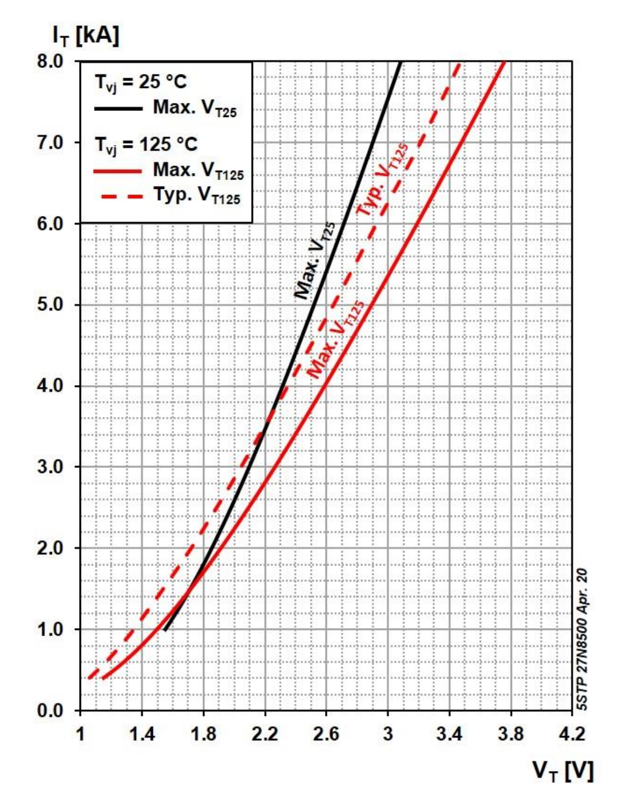


Fig. 2 On-state voltage characteristics

Max. on-state characteristic model:

$$V_{T125} = A_{Tvj} + B_{Tvj} \cdot I_T + C_{Tvj} \cdot \ln(I_T + 1) + D_{Tvj} \cdot \sqrt{I_T}$$

Valid for I_T = 400 - 70000 A

A_{125}	B_{125}	C_{125}	D_{125}
$65.47 \cdot 10^{-3}$	$219.0 \cdot 10^{-6}$	$141.7 \cdot 10^{-3}$	$7.488 \cdot 10^{-3}$

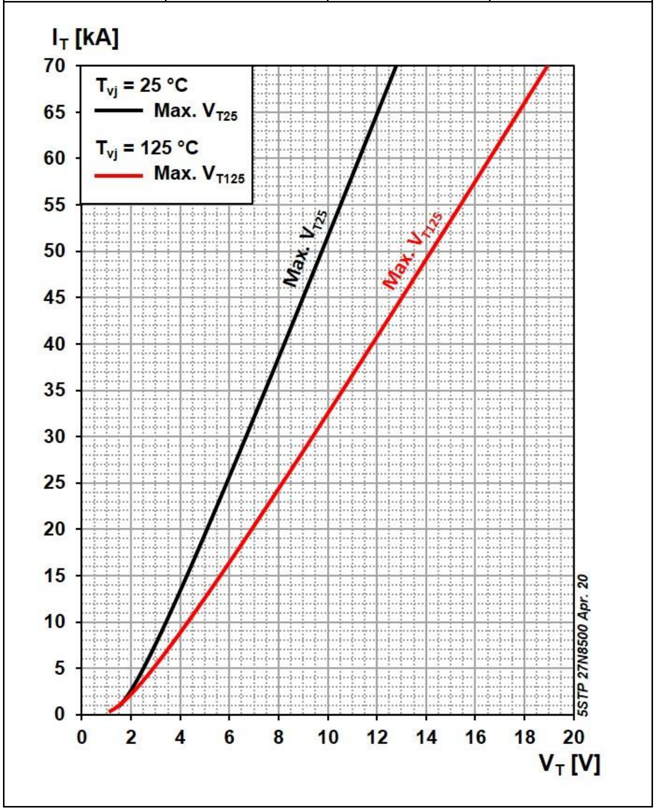


Fig. 3 On-state voltage characteristics

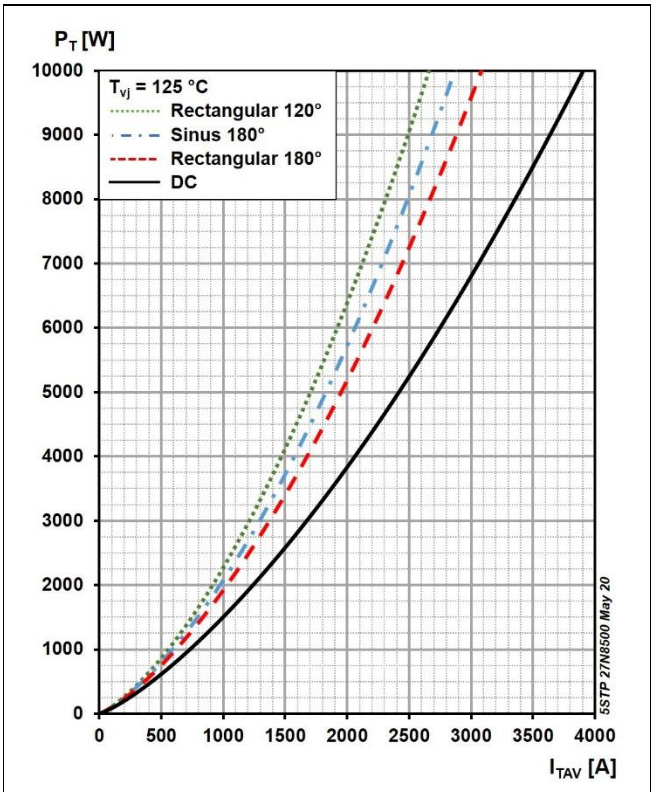


Fig. 4 On-state power dissipation vs. mean on-state current, turn-on losses excluded

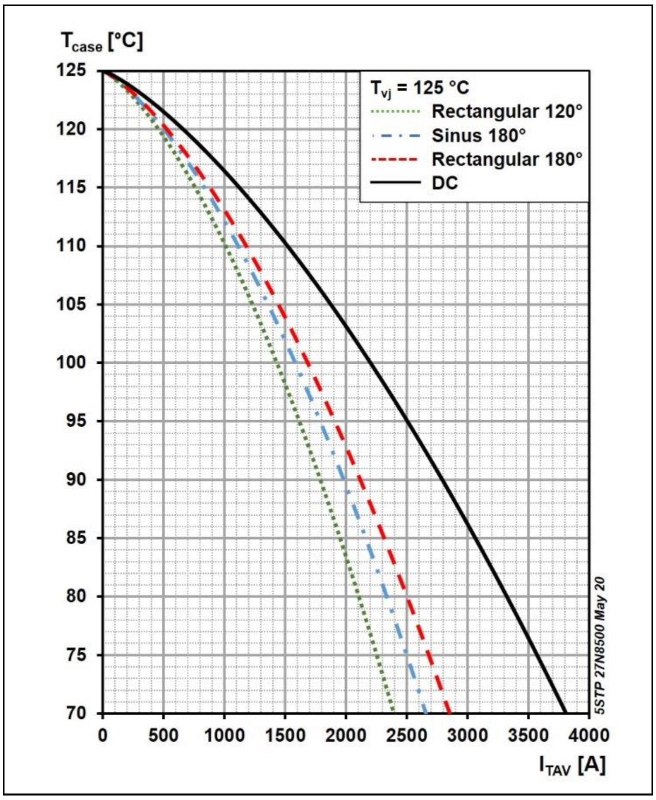


Fig. 5 Max. permissible case temperature vs. mean on-state current, switching losses ignored

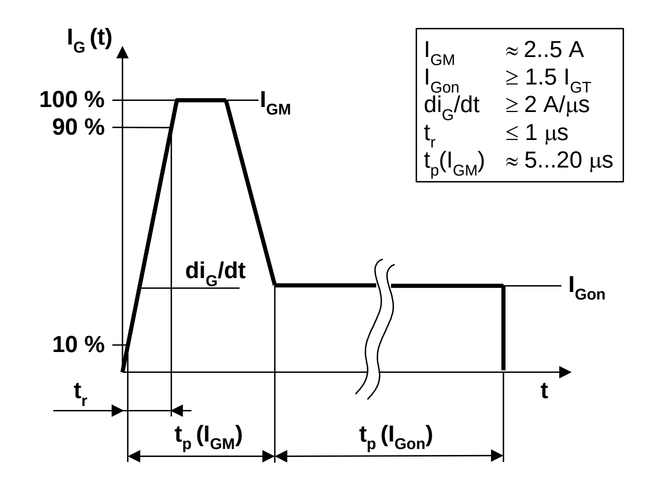


Fig. 6 Recommended gate current waveform

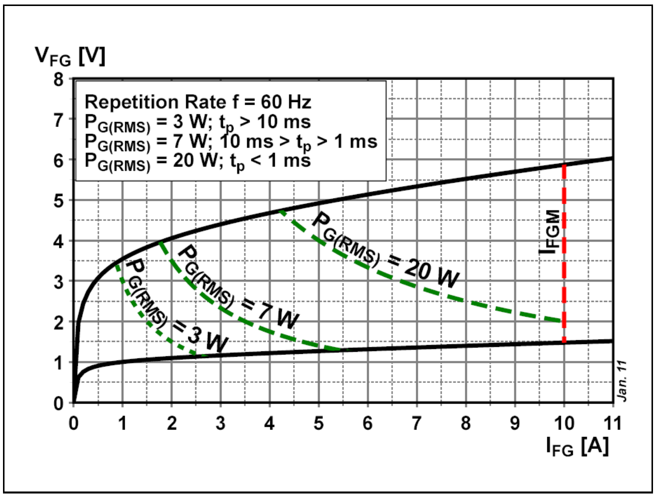


Fig. 7 Max. peak gate power loss

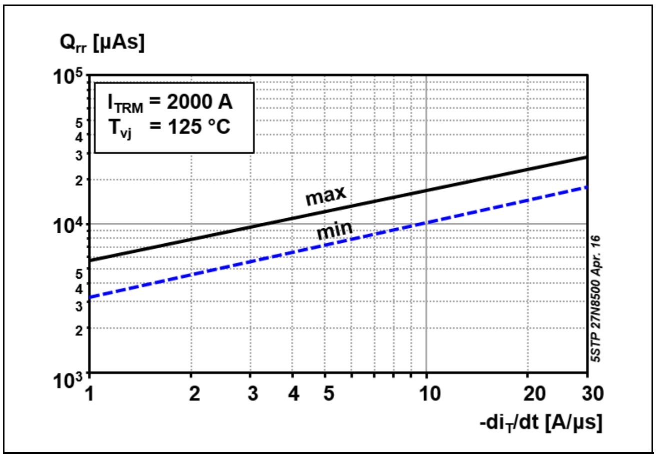


Fig. 8 Reverse recovery charge vs. decay rate of on-state current

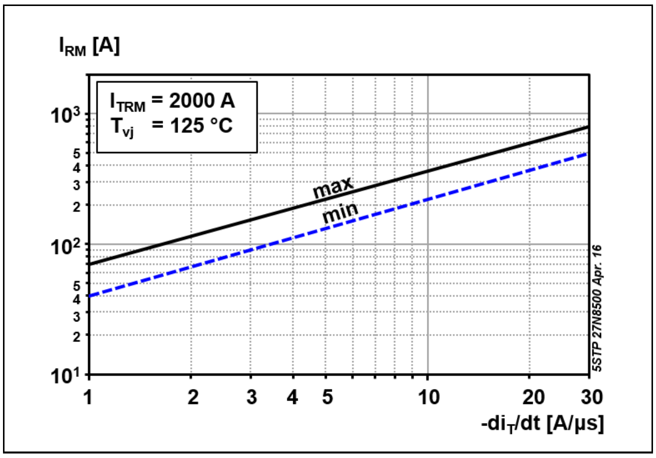


Fig. 9 Peak reverse recovery current vs. decay rate of on-state current

Power losses

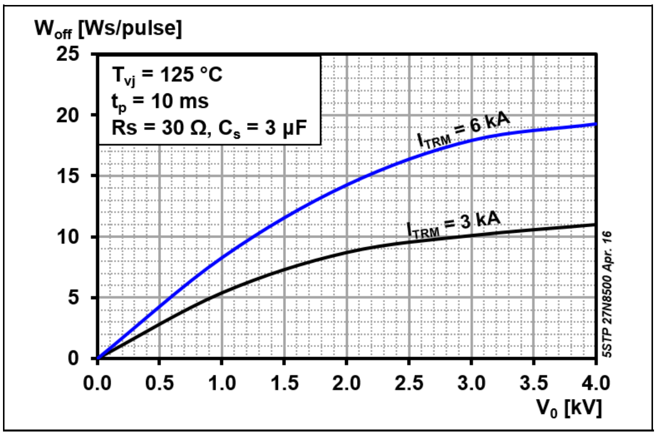


Fig. 10 Turn-off energy, half sinusoidal waves

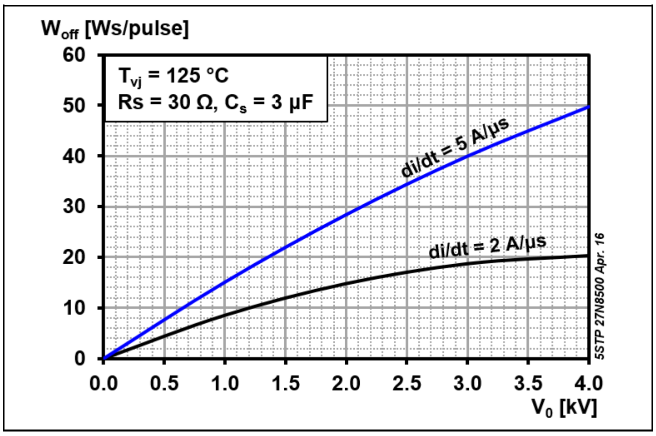


Fig. 11 Turn-off energy, rectangular waves

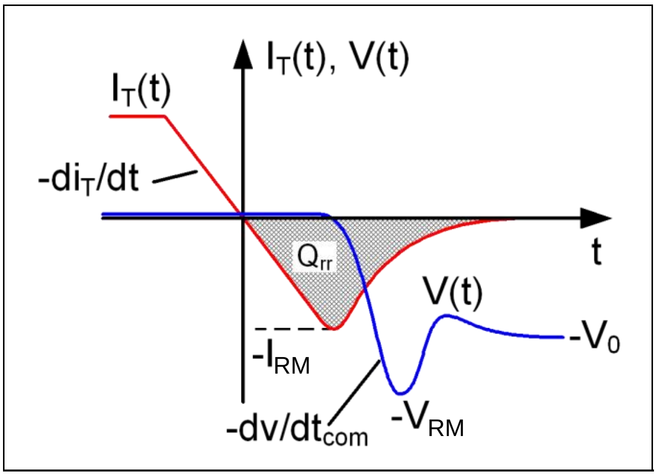


Fig. 12 Current and voltage waveforms at turn-off

Total power loss for repetitive waveforms:

$$P_{TOT} = P_T + W_{on} \cdot f + W_{off} \cdot f$$

where

$$P_T = \frac{1}{T} \int_0^T I_T \cdot V_T(I_T)\ dt$$

Fig. 13 Relationships for power loss

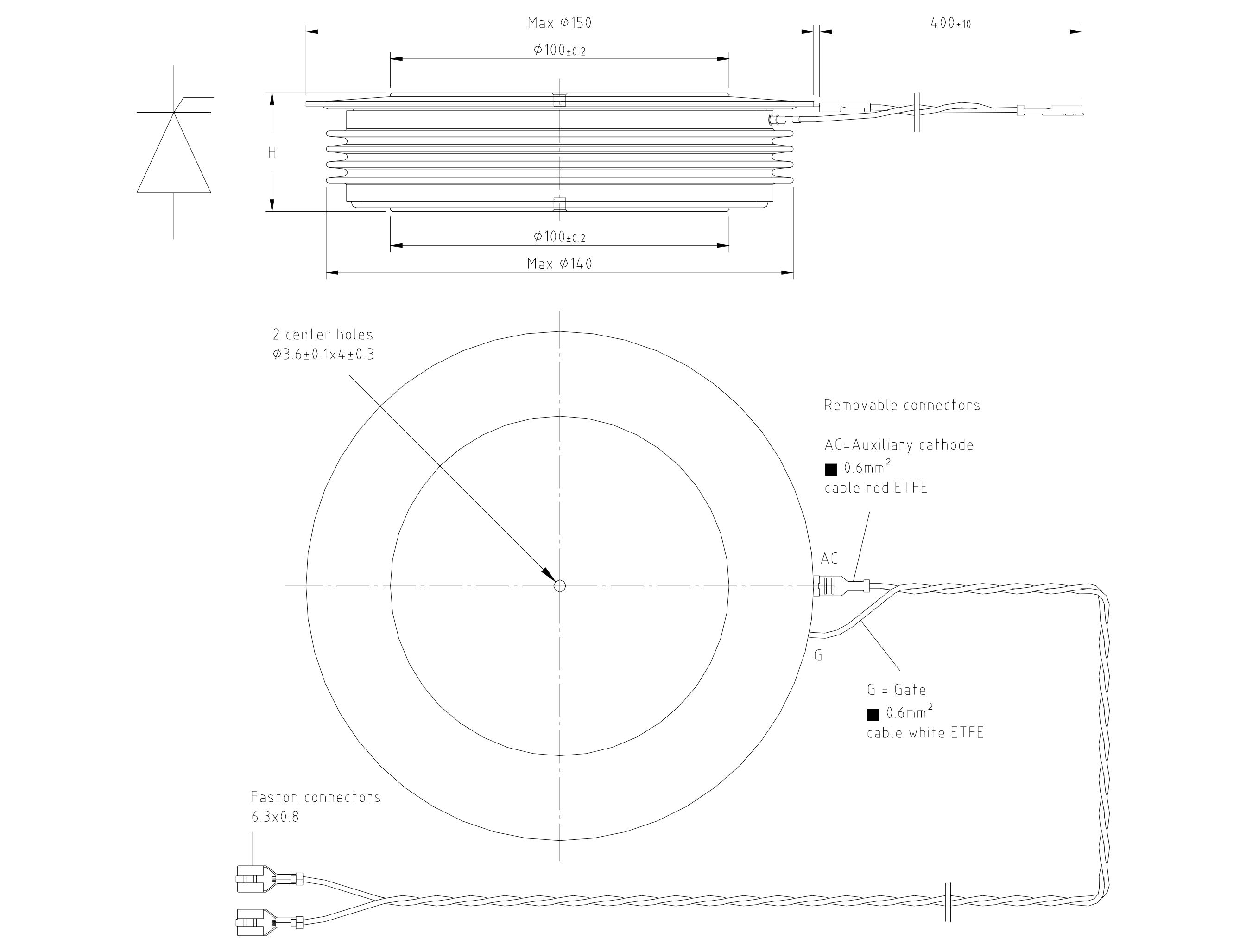


Fig. 14 Device Outline Drawing

Related documents:

5SYA 2020	Design of RC-Snubbers for Phase Control Applications
5SYA 2049	Voltage definitions for phase control and bi-directionally controlled thyristors
5SYA 2051	Voltage ratings of high power semiconductors
5SYA 2034	Gate-drive recommendations for phase control and bi-directionally controlled thyristors
5SYA 2036	Recommendations regarding mechanical clamping of Press-Pack High Power Semiconductors
5SYA 2102	Surge currents for Phase Control Thyristors
5SZK 9118	General Environmental Conditions for High Power Semiconductors

Please refer to http://www.abb.com/semiconductors for current version of documents.

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